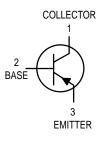
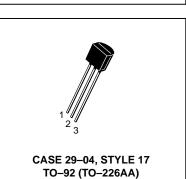
Amplifier Transistors

PNP Silicon





BC307,B,C

BC308C BC309B

MAXIMUM RATINGS

Rating	Symbol	BC 307	BC 308C	BC 309	Unit
Collector-Emitter Voltage	VCEO	-45	-25	-25	Vdc
Collector-Base Voltage	VCBO	-50	-30	-30	Vdc
Emitter-Base Voltage	VEBO	-5.0			Vdc
Collector Current — Continuous	IC	-100			mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8			mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C	
Operating and Storage Junction Temperature Range	TJ, Tstg	-55 to +150		°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta}JC$	125	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•				
Collector-Emitter Breakdown Voltage ($I_C = -2.0 \text{ mAdc}, I_B = 0$)	BC307 BC308C BC309B	V(BR)CEO	-45 -25 -25			Vdc
Emitter-Base Breakdown Voltage (I _E = -100 μAdc, I _C = 0)	BC307 BC308C BC309B	V(BR)EBO	5.0 5.0 5.0			Vdc
Collector-Emitter Leakage Current ($V_{CES} = -50 \text{ V}, V_{BE} = 0$) ($V_{CES} = -30 \text{ V}, V_{BE} = 0$)	BC307 BC308C BC309B	ICES		-0.2 -0.2 -0.2	15 15 15	nAdc
(V _{CES} = –50 V, V _{BE} = 0) T _A = 125°C	BC307		—	-0.2	-4.0	μΑ
(V _{CES} = -30 V, V _{BE} = 0) T _A = 125°C	BC308C BC309B		—	-0.2 -0.2	-4.0 -4.0	



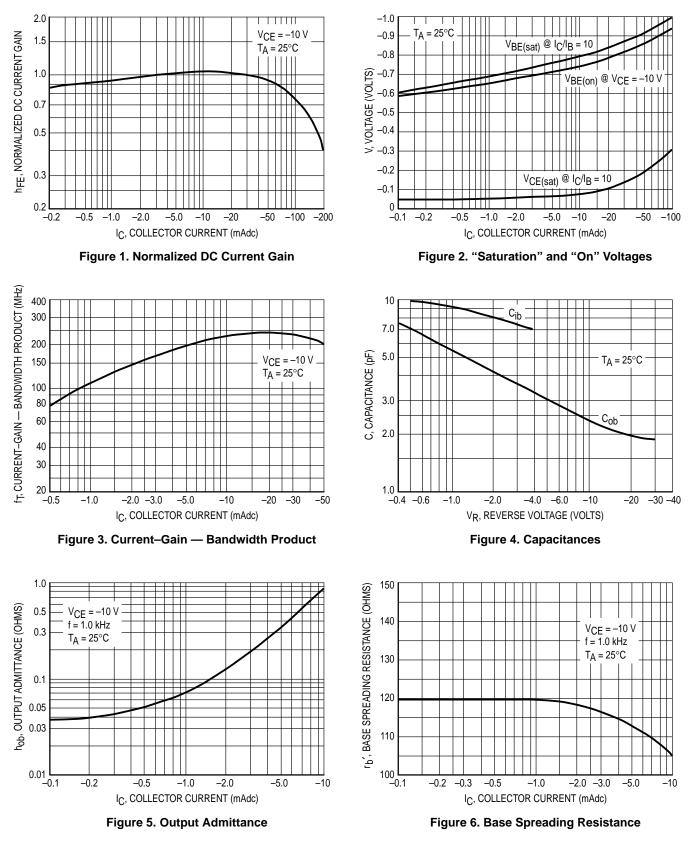
BC307,B,C BC308C BC309B

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

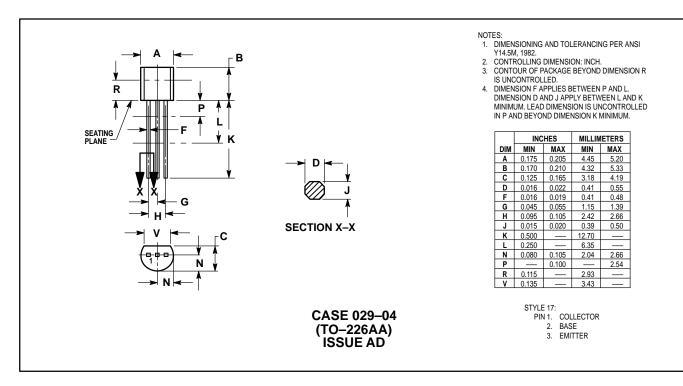
Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS				•	•	•
DC Current Gain (I _C = -10μ Adc, V _{CE} = -5.0 Vdc)	BC307B/309B BC307C/308C	hFE	_	150 270		_
$(I_{C} = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307 BC308C		120 120	_	800 800	
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307B/309B BC307C/308C		200 420	290 500	460 800	
	BC307B/309B BC307C/308C			180 300	_	
Collector-Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -0.5 \text{ mAdc}$) ($I_C = -10 \text{ mAdc}$, $I_B = \text{see Note 1}$) ($I_C = -100 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)		VCE(sat)		-0.10 -0.30 -0.25	-0.3 -0.6 	Vdc
Base – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc}$) ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		VBE(sat)		-0.7 -1.0		Vdc
Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)		VBE(on)	-0.55	-0.62	-0.7	Vdc
DYNAMIC CHARACTERISTICS		•				
Current–Gain — Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, f = 100 MHz)	BC307 BC308C BC309B	fΤ		280 320 360		MHz
Common Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{cbo}	_	—	6.0	pF
Noise Figure ($I_C = -0.2 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$, $R_S = 2.0 \text{ k}\Omega$, f = 1.0 kHz) ($I_C = -0.2 \text{ mAdc}$, $V_{CE} = -5.0 \text{ Vdc}$, $R_S = 2.0 \text{ k}\Omega$, f = 1.0 kHz, f = 200 Hz)	BC309 BC307 BC308C BC309B	NF		2.0 2.0 2.0 2.0	4.0 10 10 4.0	dB

1. I_C = -10 mAdc on the constant base current characteristic, which yields the point I_C = -11 mAdc, V_{CE} = -1.0 V.

BC307,B,C BC308C BC309B



PACKAGE DIMENSIONS



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